



PARTS HISTORY LOG

Radiation Testing

PROGRAMME:- XMM

PART TYPE:- OP604

RADIATION REPORT:- RD 225

IGG TASK NUMBER:- 1500

SUMMARY OF TEST RESULTS

Serial numbers 306 and 278 were below the minimum $I_{C(ON)}$ limit at initial measurements. Serial number 232 failed $I_{C(ON)}$ at 10kRADS and serial number 307 failed this parameter at 20kRADS. The results for I_{CBO} remained well below the maximum limit and showed no significant change throughout the test.



Radiation Report Number:- RD 225

Project:- XMM

Part Type:- OP604

Date Code:- 9603

Manufacturer:- Optek/U

IGG Task No:- 1500

Project Approval of Lot Traveller:-

Signed.....*[Signature]*.....

Date..3-6-97..

Position..Component Engineer..

Serial Number Range:-

232 through 308 (not inclusive)

I certify that the subject component has been tested in accordance with the following radiation specifications:-

Test Method - ESA/SCC22900 ISSUE- 4 DATE- Jan '95

Irradiation Test Plan- XM-PL-IGG-0058 ISSUE- 3 DATE- Mar '97

Closed/Approved NCR No:- N N/A

Approved Waiver No:- WAR N/A

Signed.....*P. Russell*.....

Date..22/5/97..

Upscreening Engineer

Signed.....*[Signature]*.....

Date..21/5/97..

Upscreening Manager



Page 3 of 7

RADIATION REPORT NUMBER:- RD 225

DATE:- 20.5.97

PROJECT:- XMM

RIR IN:- 77708

PART NUMBER:- OP604

MANUFACTURER:- Optek/U

PROCUREMENT LEVEL:- ESA/SCC5403/005

DATE CODE:- 9603

TEST METHOD:- ESA/SCC22900 ISSUE- 4 DATE- Jan '95

TEST PLAN:- XM-PL-IGG-0058 ISSUE- 3 DATE- Mar '97

START QUANTITY:- 5

No.	Test (Sample Size)	XM-PL-IGG-0058 Test Method and Conditions	Date in	Qty in	Date out	Qty out	SIGNED Op/QA
1	Serialisation and Selection of Control Sample (100%)	Control Sample= SN 308	01/05/97	5	01/05/97	4 + CONTROL SAMPLE	 IGG 16 CT
2	Initial Electrical Measurements (100% read and record)	Table A Testing at IGG	01/05/97	4	01/05/97	2	 IGG 16 CT
3	Initial Electrical Measurements (100% read and record)	Table A Testing at ERA	07/05/97	4	07/05/97	2	 IGG 16 CT
4	Set-up and apply Bias per Figure 1	Verify Bias Circuit and conditions (in-situ) for all 4 test samples	07/05/97	4	07/05/97	4	 IGG 16 CT
5	Irradiation 1 (4 samples)	Dose= 10kRAD(Si) Rate= 10RAD(Si) per second Time= 1000secs	07/05/97	4	07/05/97	4	 IGG 16 CT
6	Interim 1 Electrical Measurements (100% read and record)	Table A. Bias to be maintained until testing is performed. Tdwel=10mins maximum	07/05/97	4	07/05/97	1	 IGG 16 CT



Report No: RD 225		Part Type: OP604			Date: 20.5.97		
No.	Test (Sample Size)	XM-PL-IGG-0058 Test Method and Conditions	Date in	Qty in	Date out	Qty out	SIGNED Op/QA
7	Irradiation 2 (4 samples)	As Test 5	07/05/97	4	07/05/97	4	 IGG 16 CT
8	Interim 2 Electrical Measurements (100% read and record)	As Test 6	07/05/97	4	07/05/97	0	 IGG 16 CT
9	Irradiation 3 (4 samples)	As Test 5	07/05/97	4	07/05/97	4	 IGG 16 CT
10	Interim 3 Electrical Measurements (100% read and record)	As Test 6	07/05/97	4	07/05/97	0	 IGG 16 CT
11	Irradiation 4 (4 samples)	Dose= 20kRAD(Si) Rate= 10RAD(Si) per second Time=2000secs	07/05/97	4	07/05/97	4	 IGG 16 CT
12	Interim 4 Electrical Measurements (100% read and record)	As Test 6	07/05/97	4	07/05/97	0	 IGG 16 CT
13	Irradiation 5 (4 samples)	Dose= 25kRAD(Si) Rate= 10RAD(Si) per second Time=2500secs	07/05/97	4	07/05/97	4	 IGG 16 CT
14	Interim 5 Electrical Measurements (100% read and record)	As Test 6	07/05/97	4	07/05/97	0	 IGG 16 CT
15	Irradiation 6 (4 samples)	As Test 13	07/05/97	4	07/05/97	4	 IGG 16 CT



Report No: RD 225		Part Type: OP604			Date: 20.5.97		
No.	Test (Sample Size)	XM-PL-IGG-0058 Test Method and Conditions	Date in	Qty in	Date out	Qty out	SIGNED Op/QA
16	Final Electrical Measurements (100% read and record)	As Test 6 At ERA	07/05/97	4	07/05/97	0	<i>P.P.R.</i> IGG 16 CT
17	Annealing Test (4 samples)	Bias for 24hrs min at +25°C (record exact time)	07/05/97	4	08/05/97	4	<i>P.P.R.</i> IGG 16 CT
18	Post Annealing Electrical Measurements (100% read and record)	Table A	08/05/97	4	08/05/97	0	<i>P.P.R.</i> IGG 16 CT
19	Accelerated Aging under bias (4 samples)	168 hours bias at +100±5°C	08/05/97	4	15/05/97	4	<i>P.P.R.</i> IGG 16 CT
20	Post Aging Electrical Measurements (100% read and record)	Table A	16/05/97	4	16/05/97	0	<i>P.P.R.</i> IGG 16 CT
21	Test Report Collation				21/5/97		<i>P.P.R.</i> IGG 2 CT
22	Test Report Approval				21/5/97		<i>P.P.R.</i> IGG 2 CT
23	NOTES:-						



FAILURE LIST AND APPLICABLE NCR

Test No.	Serial Number(s)	Failed Parameter and Failure Mode	Applicable NCR
2	278, 306	FAILED $I_c(ON)$.	-
6	232	FAILED $I_c(ON)$.	-
8	307	FAILED $I_c(ON)$.	-

I.G.G. COMPONENT TECHNOLOGY LTD.

REPORT NO. RD225

PART TYPE OP 604 OPTION _____

SHEET 9 OF 10

ELECTRICAL MEASUREMENTS w.r.t. XM-PL-166-0058

Table A

Parameter Serial No's	I _{CEO} (pA)	I _{c(ON)} (mA)					
CONTROL 308	182	9.82					
232 (Pos: 1)	462	3.44	FAIL				
307 (Pos: 2)	478	4.02	FAIL				
306 (Pos: 3)	442	2.48	FAIL				
278 (Pos: 4)	732	2.04	FAIL				
Limit	≤ 25 nA	≥ 7.0 mA					
Condition	V _{CE} = 10V	V _{CE} = 5V					

Measured by P.A. Russell

Date 8TH MAY 1997

Test Equipment used:-

EQUIPMENT

CT NUMBER

TEKTRONIX 370 CURVE TRACER

CT217



RADIATION TEST SUMMARY

PART TYPE : OP604

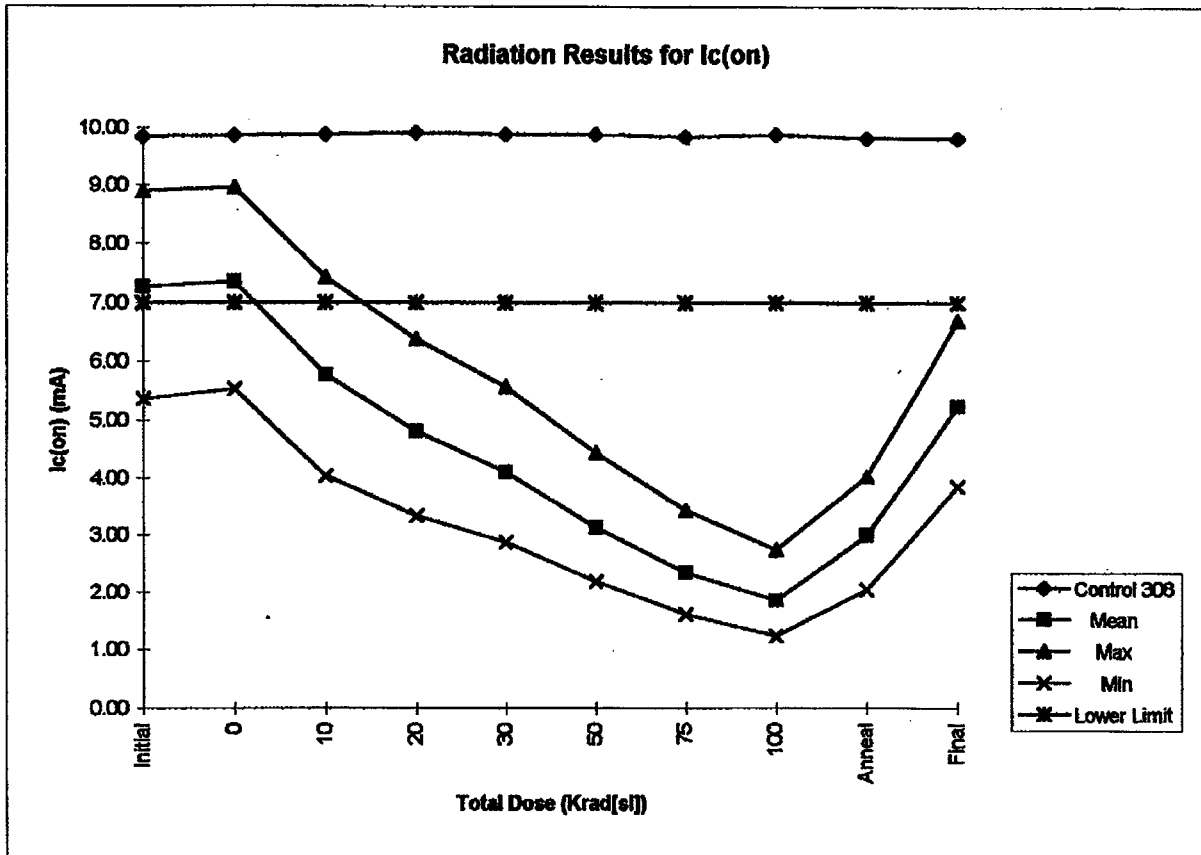
DESCRIPTION : HI-REL NPN PHOTOTRANSISTOR

REPORT NO. : RD 225

PARAMETERS PLOTTED :

$I_c(on)$


NOTE : The results for I_{ceo} showed no significant change and hence a plot was not considered necessary.



Dose (kRad)	Control 308 (mA)	Mean (mA)	Max (mA)	Min (mA)	Lower Limit (mA)	Upper Limit (mA)	Std.Dev.
Initial	9.84	7.29	8.90	5.38	7.0	-	1.58
0	9.86	7.36	8.96	5.54	7.0	-	1.55
10	9.88	5.78	7.44	4.04	7.0	-	1.48
20	9.92	4.81	6.38	3.34	7.0	-	1.31
30	9.88	4.11	5.58	2.88	7.0	-	1.17
50	9.88	3.13	4.44	2.19	7.0	-	1.00
75	9.84	2.35	3.43	1.61	7.0	-	0.83
100	9.88	1.86	2.74	1.23	7.0	-	0.69
Anneal	9.82	3.00	4.02	2.04	7.0	-	0.90
Final	9.82	5.24	6.68	3.84	7.0	-	1.24

Lot size for statistics : 4 devices

RD 225 Date code 9603

	IRRADIATION TEST PLAN NO. XM-PL-IGG-0058	Issue No. 3 Date: March 1997 Page: 1/4
-----------------------------------------------------------------------------------	----------------------------------------------------	-------------------------------------------------------------------

Component No. ESA/SCC 5403/05	Component Designation: Hi-Rel NPN Phototransistor Type: OP604	Irradiation Spec No. N/A Iss. Rev.
-----------------------------------------	----------------------------------------------------------------------------	---------------------------------------------------------------------

Specification Generic: ESA/SCC 5000 Iss. 8 Detail: ESA/SCC 5403/05 Draft D	Acceptance Evaluation — Element — Diffusion — Lot <u> X </u>	Electrical Meas. In-situ — Remote <u> X </u>	Project/Programme XMM
--------------------------------------------------------------------------------------------------------	--------------------------------------------------------------------------------------------------------------	----------------------------------------------------------------------------	-----------------------------------------------------------------------------------------------

Manufacturer: Optek Technology Inc. Address: 1215 W. Crosby Road Carrollton Texas 75006	Test Facility: ERA Address: Leatherhead Surrey ENGLAND	Originator: IGG CT Name: J. Arnold
----------------------------------------------------------------------------------------------------------------	-------------------------------------------------------------------------------	-----------------------------------------------------

Radiation Source: COBALT 60	Sample Size: 4 Control Devices: 1	Exposure: Single — Multiple <u> X </u>	Annealing Test: YES <u> X </u> NO —	Radiation Level: 10kRAD(Si), 50kRAD(Si) 20kRAD(Si), 75kRAD(Si) 30kRAD(Si), 100kRAD(Si)
-------------------------------------------	--------------------------------------------------------	------------------------------------------------------------------	-----------------------------------------------------	--------------------------------------------------------------------------------------------------------

Single Exposure: Dose [kRAD(Si)] Dose Rate [RAD(Si)/s] Exposure Time Not Applicable	Multiple Exposure: <table border="1" style="width:100%; border-collapse: collapse; margin-top: 10px;"> <thead> <tr> <th style="width:20%;">Irradiation Steps</th> <th style="width:10%;">1</th> <th style="width:10%;">2</th> <th style="width:10%;">3</th> <th style="width:10%;">4</th> <th style="width:10%;">5</th> <th style="width:10%;">6</th> </tr> </thead> <tbody> <tr> <td>Dose [kRAD(Si)]</td> <td>10</td> <td>10</td> <td>10</td> <td>20</td> <td>25</td> <td>25</td> </tr> <tr> <td>Dose Rate [RAD(Si)/s]</td> <td>10</td> <td>10</td> <td>10</td> <td>10</td> <td>10</td> <td>10</td> </tr> <tr> <td>Exposure Time (secs)</td> <td>1000</td> <td>1000</td> <td>1000</td> <td>2000</td> <td>2500</td> <td>2500</td> </tr> </tbody> </table>	Irradiation Steps	1	2	3	4	5	6	Dose [kRAD(Si)]	10	10	10	20	25	25	Dose Rate [RAD(Si)/s]	10	10	10	10	10	10	Exposure Time (secs)	1000	1000	1000	2000	2500	2500
Irradiation Steps	1	2	3	4	5	6																							
Dose [kRAD(Si)]	10	10	10	20	25	25																							
Dose Rate [RAD(Si)/s]	10	10	10	10	10	10																							
Exposure Time (secs)	1000	1000	1000	2000	2500	2500																							

Bias Requirements: During Exposure (for in-situ electrical measurements): N/A
 During and after Exposure (for remote electrical measurements): YES

Bias Conditions:
Test Circuits: The Electrical Bias circuit is given in Figure 1 herein.
 Voltages: See Figure 1 Tolerance: See Figure 1

Shielding: Shielding is required to minimize dose enhancement effects caused by low energy, scattered radiation. The test specimens shall be enclosed in a Pb/Al container of Pb 1.5mm minimum, surrounding an inner shield of 0.7 to 1.0mm Al.

Irradiation Test Sequence

Test Step	Description	Requirements
1	Serialization Goods Receiving Inspection	If parts are not serialized, serialize them (permanently) sequentially from 1 to 5 inclusive.
2	Initial Electrical Measurements at Room Temperature only	Per Table A herein.
3	Set-up of Test	Verify Figure 1 Bias Circuit and Voltages (In-situ) for all 5 test samples.
4	Irradiation Exposure	Verify radiation dose rate and position in the chamber to achieve required dose. Verify and witness duration of exposure to achieve required dose.



XMM

IRRADIATION TEST PLAN NO.

XM-PL-IGG-0058

Issue No. 2

Date: February 1997

Page: 2/4

1

2

Irradiation Test Sequence (Cont.)

21

Test Step	Description	Requirements
5	Intermediate Electrical Measurements	Bias to be maintained until measurements are performed. Test per Table A herein - (Read and Record) - on all 5 parts. Test to be performed immediately upon removal from chamber (less than 10 mins interval). Upon completion of test devices to be replaced in bias circuit (4 parts) and returned to chamber. Maximum interval between two consecutive exposures to be 30 mins.
6 to 21	Repeat Set-up/Exposure/Test sequence upto Total Dose of 100kRAD(Si) as per Plan above.	Repeat Steps 3, 4, 5 for a total of 6 cycles upto the total dose of 100kRAD(Si) at accumulated doses of 10, 20, 30, 50, 75 and 100kRAD(Si). (See Remark 2).
22	Annealing	To be 24 hours at +25°C under Figure 1 bias.
23	Accelerated Ageing under Bias	Bake at +100°C under Figure 1 bias for 168 hours.
24	Final Electrical Measurements	Per Table A herein - (Read and Record) - on all 5 parts.
25	Total Dose Irradiation Test Report	ESA/SCC No. 22900.

Remarks

22

1. Performed for the purposes of correlation.
2. The set up exposure/test sequence shall be stopped for any device that exhibits repeated functional failure.
3. Electrical testing shall be performed on the same test equipment from test step 2 through 24.



XMM

IRRADIATION TEST PLAN NO.

XM-PL-IGG-0058

Issue No. 2

Date: February 1997

Page: 3/4

1

2

TABLE A - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - $T_{amb} = +25 \pm 5^{\circ}C$ BEFORE, AT INTERMEDIATE POINTS AND ON COMPLETION OF IRRADIATION

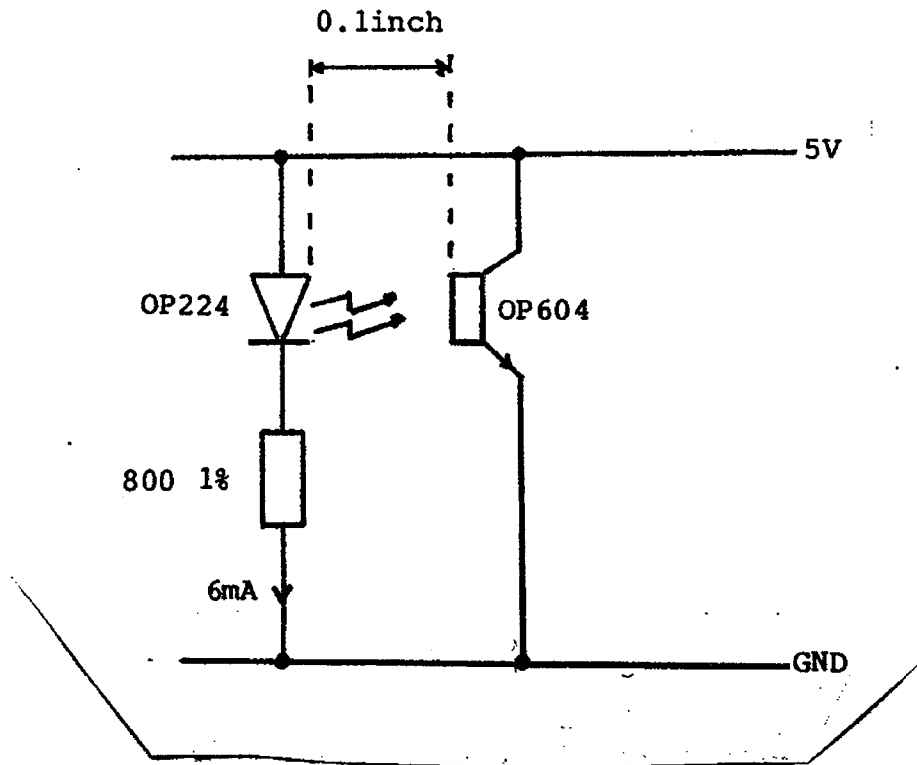
NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD-750	TEST CONDITIONS	LIMITS		UNIT
					MIN.	MAX.	
1	Dark Current	I_{CEO}	3041	$V_{CE} = 10.0Vdc$	-	25	mA
2	On-State Collector Current	$I_{C(ON)}$	-	$V_{CE} = 5.0Vdc$ $E_s = 20mW/cm_2$ (Note 1)	7.0	-	mA

NOTES:

1. Light source is an unfiltered tungsten lamp operating at $CT = 2870K$ or equivalent source.



FIGURE 1 - ELECTRICAL CIRCUIT FOR IRRADIATION TESTING





NON-CONFORMANCE REPORT

SHEET 1 OF

XM-NC-IGG-0552

NO: N51552

INITIATOR: SL

TASK NO: 1500

DATE: 1.7.97

MANUFACTURER/COUNTRY: OPTEK / u.

RIR: 77708 d 77707

SUPPLIER/COUNTRY:

PART TYPE: 0P224 & 0P604

VALUE:

DETAIL SPECIFICATION: XM-PL-IGG-0058

ISSUE: 3

COMPONENT NUMBER: 0P224S & 0P604S

PROJECT REFERENCE: (if applicable)

P.O. NO: CT 11876

PLIN NO: 151233 (0P224) & 151252 (0P604)

P.O. ITEM No: (if no RIR)

SAR:

LOT NO:

DATECODE: 4539 & 9603

N.C. DETECTED AT: RADIATION TESTING

QUANTITY: 5

DURING: E.M. Ic (on)

SERIAL NO: (or Range:)

DETAILS OF NON-CONFORMANCE: (INCLUDING PRELIMINARY DISPOSITION)

TWO ^{FROM} PARTS (65 PCS) FAILED INITIAL E.M. ON IC (GW) PARAMETER.
 ALL PARTS FAILED IC (on) AT 20 KEADS. DORNIER REQUEST NCR TO BE RAISED.
 DOR/ESA/ALENIA / MMS ST INFORMED REF JEM-XM-FX-IGG-5693.
 DATED 1.7.97. ADMIT MMS ST & DORNIER RESPOSE.

[Signature] 1.7.97

USER (MMS) / DORN / ESA / ALENIA ADVISED OF RADIATION RESULTS (RD 225) AND REQUESTED TO SUPPLY COMMENTS REF. XM-FX-IGG-5693

MMS/S - ACCEPT REF XM-MMS-146-97 DATED 21-7-97
 DORN - ACCEPT REF PCB 26 XM-MMS-IGG-5810 DATED 23-7-97
 ESA - _____
 ALENIA - _____

FINAL DISPOSITION:

MAJOR:

MINOR:

ACCEPT AS IS M. Wakelin 29-7-97

MRB BOARD: M. WAKELIN D. GRUCKY



SIGNED (CHAIRMAN MRB):

M. Wakelin

DATE: 29-7-97

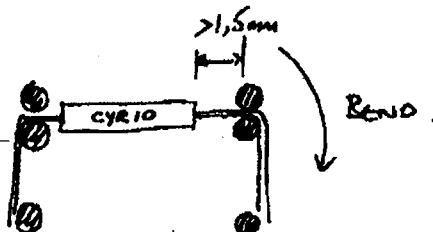
REPORT REFERENCE (or N/A):

N/A

TO /A: M Wakelin	COMPANY/SOCIETE: IGG Component Technology FAX 01329.82.9312
FROM/DE: M Roe (MMS)	COPIES TO: ESTEC A Eiding Fax 00.31.71.888.4886 DS T Standberg Fax 00.48.78488.4188 ALENIA P Santoro Fax 00.39.11.7180.637 MMS(B) P Airey Fax 8883 MMS(S) P McMahon SPC F476 RJ Davies SPC F486 A Ward Fax 3418
DATE: 21 July, 1997	
This facsimile consists of 1 pages, this number includes this page Cet envoi comprend pages, ce nombre inclut cette page	If you do not receive legible copies of all pages, please telephone immediately. Si vous n'avez pas reçu clairement cet envoi veuillez nous contacter par téléphone au: +44 (0) 14 38 77 33 70
Direct lines: Fax : +44 (0) 1438 773778 Phone : +44 (0) 1438 773330	
SUBJECT/OBJET: XMM Parts Non-Conformance N51526	REF: XM.MMS.146.97

- Reference documents:
- (1) XMM Project identification XM.NC.IGG.0526
 - (2) PCB 25
 - (3) IGG Fax XM.FX.IGG.5742
 - (4) IGG fax XM.FX.IGG.5673 (OP604 RVT)
 - (5) IGG fax XM.FX.IGG.5595 (CYR20 5n1)

In response to subject fax (1)..(3) above which relates to the lead bending and package cracking of CYR10/180pF capacitor, MMS has reviewed the lead bending and forming criterion applied to the component in order to mount it on the PCB, with the following results:-



As can be seen from the above figure, the leads will be supported close to the component body, and will be bent a minimum of approximately 1mm from the glass body. Note that the wire diameter is $0.49 < \varnothing < 0.61$ mm. Tooling at MMS ensures the lead length close to the body is held stable. I trust this provides sufficient information to assess suitability of the procured parts.

Regarding OP604 RVT (ref (4)), MMS can confirm the degradation is in line with expected values used in the Worst case analysis, and we therefore can accept these parts.

With regard to failure of CYR20 glass capacitors, and in response to (5) above, MMS cannot accept these parts until we are satisfied that they are fit for Flight. IGG proposal to conduct life test would therefore be a sensible approach. Unfortunately this is likely to impact on the already critical schedule, and therefore MMS suggests that alternatives may be a quicker solution. We could accept 4.7nF value in lieu of the 5.1nF. Could IGG please advise recommended way forward.

Best Regards,

Mark W B Roe



**IGG Component
Technology Ltd.**
Waterside House
Waterside Gardens
Fareham
PO16 8RR England

TEL: +44 1329 829311
FAX: +44 1329 829312
TELEX: +51 86727

X M M

XMM Reference: XM-FX-IGG-5673
IGG Fax Ref.: D77825
Date: 1st July 1997

TO: DORNIER : U. GAGEUR/K. HAAS
ESA : J. MINNEE/J. VAN DOOREN/R. THOMAS/R. LAINE
ALENIA : P. SANTORO/P. PEZZELLA
MMS, St : M. ROE

COPY: IGG : D. GRUCHY/M. WAKELIN

SUBJECT: XMM - PARTS NON-CONFORMANCE

XMM Project Identification: XM-NC-IGG-0552

1. NCR INTRODUCTION

Title : RVT non-compliance
Part Type : OP224 and OP604
Component No. : OP224S and OP604S
Lot/Date Code : OP224 = 9539 and OP604 = 9603
Manufacturer : Optek, USA
NCR Level : 1 (Major)
User(s) : MMS, Stevenage

2. NON-CONFORMANCE DESCRIPTION

Stated During : RVT Testing
Location : IGG
Date Raised : 1st July 1997
Description : RVT Testing in accordance with Irradiation Test Plan No. XM-PL-IGG-0058 Issue 3 (application test/biasing) recorded parametric $I_{C(ON)}$ failure at initial testing. On 2 OP224/OP604 pair, parts failed Radiation Test Plan limit of 7.0mA min. This parameter degraded with total dose until all samples failed at 20kRADS.

X M M

XMM Reference: XM-FX-IGG-5673

IGG Fax Ref.: D77825

Page 2

3. IGG's PROPOSED DISPOSITION

User to review Total Dose Test Data Report No. RD225, and advise Dornier of proposed corrective action on application.

4. FURTHER MRB DISPOSITION REQUIRED FROM:

MMS, Stevenage and Dornier.

Best regards



S. LUK

Fax/Télécopie

MATRA MARCONI SPACE

TO/A: D Gruchy	COMPANY/SOCIETE: IGG Component Technology FAX 01329.820912....
FROM/DE: M Roe (MMS)	COPIES TO : Dornier Syst T Standberg 00 40 70400 4100 ESTEC A Bivling) 00 31 71 000 4000 J Mince) MMB M Nixon / P Alroy (XMM)) 0203 N Marshall (XMM)) M Brewer / M Burton (INTEGRAL)) MMS P McMahon SPC F470 RJ Devise SPC F400 A Ward SPC F400
DATE: 2 December, 1996	
This facsimile consists of 3 pages, this number includes this page Cet envoi comprend 3 pages, ce nombre inclut cette page	If you do not receive legible copies of all pages, please telephone immediately. Si vous n'avez pas reçu clairement cet envoi veuillez nous contacter par téléphone au: +44 (0) 14 38 77 33 70
Direct lines: Fax : +44 (0) 1438 773778 Phone : +44 (0) 1438 773330	
SUBJECT/OBJET: XMM/Integral Optos (OP604/OP224)	REF: XM-MMS-0182-96

28/11 10h20

Further to your Fax (ref XM.FX.IGG.3650), regarding the radiation tolerance of the OP604 and OP224 devices.

MMS (and BAe formally) have used these parts for many years in Spacoflight hardware, and so have accumulated several Radiation reports regarding the hardness issue.

It is the view of MMS that the OP604 specifically, (being a two terminal photo-transistor) is susceptible to cumulative dose radiation, and would not meet its procurement specification limits at 100Krad. Conversely the OP224 is a GaAs LED, and therefore may be considered to be rad-hard.

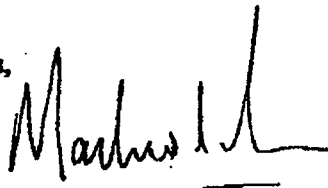
I append for your information, a page from a recent MMS Radiation report for these devices - when tested as a discrete opto-coupler under conditions similar to that seen in the XMM/INTEGRAL RWA application.

As you can see the 'coupled gain' Ic/If falls off with radiation, to approx. 50% at 100Krad.

In view of the above, I am surprised that the recent XMM PCB classified these parts as "...insensitive".

I await your response.

Best Regards,



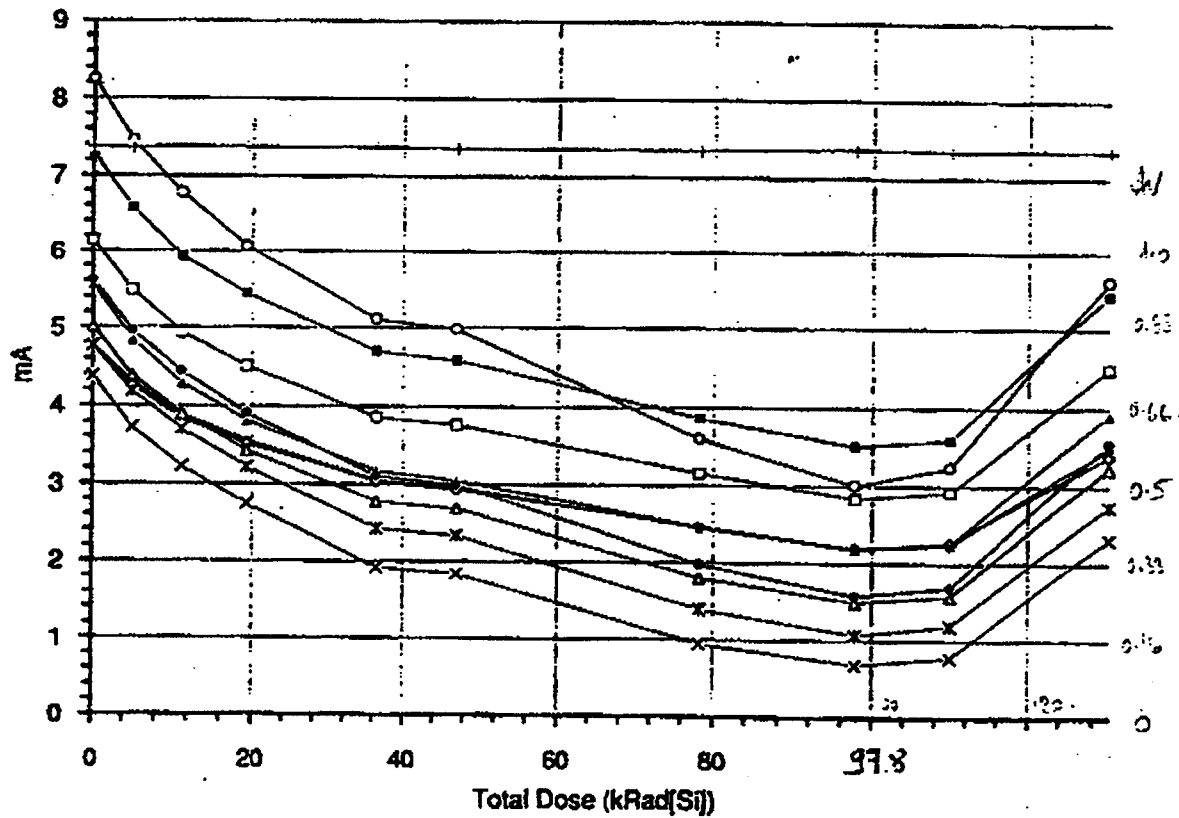
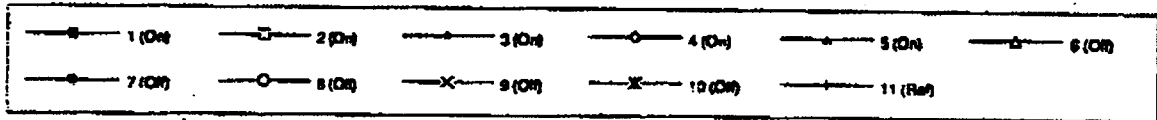
Mark W B Roe

OP224
5402/1005

Total Dose Radiation Testing

MATRA MARCONI SPACE

Date: December 95.		Fig. 7
Type: PAIR OP604/224	Date Code:	Manufacturer: OPTEK
Tested Parameter: Ic(6mA)	Radiation Source: Co60 <small>10 mdo/sec</small>	
	Dose Rate: ≤ 0.36 kRad/h.	
Test Conditions: Vce=5V, If=6mA.		
Irradiation Conditions: Static On(Sn1 to 5), Off(Sn6 to 10).	Number of irradiated devices: 10	



The two last points correspond to the post annealing measurements.

Reference: DOF/DEC/RP6.010
 Issue: 00
 Date: 04/01/96
 Page: 6/10

II.3 EXPERIMENTAL CONDITIONS

IRRADIATION FACILITY	
Place:	MATRA VELIZY (France)
Type:	Cobalt 60 Shepherd 484
Activity:	9 Curies
Calibration Date:	09/09/95
EXPOSURE TYPE	
Type:	Multiple Exposures
Steps:	5.1, 11.2, 19.3, 36.4, 47, 78.2, 97.8 kRad[Si].
BIASING CONDITIONS	
COMMENTS	
<p>5 pairs were biased in Static On mode 5 pairs in Static Off mode with all pins connected to ground.</p>	